FAIRCHILD SEMICONDUCTOR®

March 2013

FDT1600N10ALZ

N-Channel PowerTrench® MOSFET

100 V, 5.6 A, 160 mΩ

Features

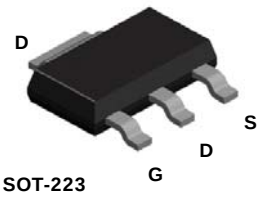
- $R_{DS(on)}$ = 121 mΩ at V_{GS} = 10 V, I_D = 2.8 A
- $R_{DS(on)}$ = 156 mΩ at V_{GS} = 5 V, I_D = 1.8 A
- Low Gate Charge (Typ.2.9 nC)
- Low C_{rss} (Typ. 2.04 pF)
- Fast Switching
- 100% Avalanche Tested
- Improved dv/dt Capability
- RoHS Compliant

Description

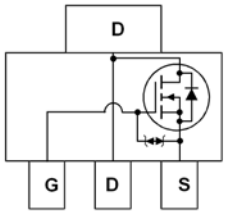
This N-Channel MOSFET is produced using Fairchild Semiconductor®'s advanced PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- Consumer Appliances
- LED TV and Monitor
- Synchronous Rectification
- Uninterruptible Power Supply
- Micro Solar Inverter



SOT-223



MOSFET Maximum Ratings T_C = 25 °C unless otherwise noted

Symbol	Parameter			FDT1600N10ALZ	Unit
V_{DSS}	Drain to Source Voltage			100	V
V_{GSS}	Gate to Source Voltage			±20	V
I_D	Drain Current	- Continuous (T_C = 25 °C)		5.6	A
		- Continuous (T_C = 100 °C)		3.5	
I_{DM}	Drain Current	- Pulsed	(Note 2)	11.2	A
E_{AS}	Single Pulse Avalanche Energy		(Note 3)	9.2	mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 4)	6.0	V/ns
P_D	Power Dissipation	(T_C = 25 °C)		10.42	W
		- Derate above 25 °C		0.083	°C
T_J, T_{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds			300	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	(Note 1)	12	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max	(Note 1a)	60	

Package Marking and Ordering Information

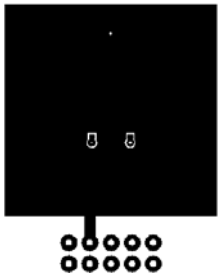
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
16010ALZ	FDT1600N10ALZ	SOT-223	13 "	12 mm	2500 units

Electrical Characteristics T_J = 25 °C unless otherwise noted

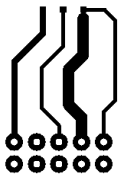
Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	100	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C	-	0.1	-	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 80 V, V_{GS} = 0V	-	-	1	μA
		V_{DS} = 80 V, V_{GS} = 0V, T_C = 125 °C	-	-	500	
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V	-	-	±10	μA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	1.4	-	2.8	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 2.8 A	-	121	160	mΩ
		V_{GS} = 5 V, I_D = 1.8 A	-	156	375	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 10 V, I_D = 5.6 A	-	26.1	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 50 V, V_{GS} = 0 V, f = 1MHz	-	169	225	pF
C_{oss}	Output Capacitance		-	43	55	pF
C_{rss}	Reverse Transfer Capacitance		-	2.04	-	pF
$C_{oss(er)}$	Energy Related Output Capacitance	V_{DS} = 50 V, V_{GS} = 0 V	-	85	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	V_{GS} = 10 V; V_{DD} = 50 V, I_D = 5.6 A	-	2.9	3.77	nC
$Q_{g(tot)}$	Total Gate Charge at 5V	V_{GS} = 5 V; V_{DD} = 50 V, I_D = 5.6 A	-	1.6	2.08	nC
Q_{gs}	Gate to Source Gate Charge	V_{DD} = 50 V, I_D = 5.6 A	-	0.7	-	nC
Q_{gd}	Gate to Drain “Miller” Charge	V_{DD} = 50 V, I_D = 5.6 A	-	0.64	-	nC
$V_{plateau}$	Gate Plateau Volatge	V_{DD} = 50 V, I_D = 5.6 A (Note 5)	-	3.81	-	V
Q_{sync}	Total Gate Charge Sync.	V_{DS} = 0V, I_D = 2.8A (Note 6)	-	2.45	-	nC
Q_{oss}	Output Charge	V_{DS} = 50V, V_{GS} = 0V	-	5.2	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 50 V, I_D = 5.6 A, V_{GS} = 10 V, R_{GEN} = 4.7 Ω	-	7.4	24.8	ns
t_r	Rise Time		-	2.5	15	ns
$t_{d(off)}$	Turn-Off Delay Time		-	13.5	37	ns
t_f	Turn-Off Fall Time	(Note 5)	-	2.4	14.8	ns
ESR	Equivalent Series Resistance(G-S)	f = 1MHz	-	2.1	-	Ω
Drain-Source Diode Characteristics						
I_S	Maximum Continous Drain to Source Diode Forward Current		-	-	5.6	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	11.2	A
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_{SD} = 5.6A	-	-	1.3	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_{SD} = 5.6A, V_{DD} = 50V, dI_F/dt = 100A/μs	-	34.1	-	ns
Q_{rr}	Reverse Recovery Charge		-	32.7	-	nC

NOTES:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 60 °C/W when mounted on a 1 in^2 pad of 2 oz copper



b) 118 °C/W when mounted on a minimum pad of 2 oz copper

2. Repetitive Rating: Pulse width limited by maximum junction temperature
3. Starting T_J = 25 °C, L = 3 mH, I_{AS} = 2.47 A
4. I_{SD} ≤ 5.6A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
5. Essentially Independent of Operating Temperature Typical Characteristics
6. See the test circuit in page 8

Typical Performance Characteristics

Figure 1. On-Region Characteristics

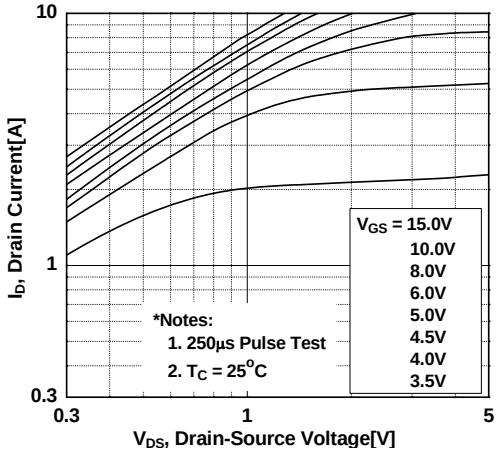


Figure 2. Transfer Characteristics

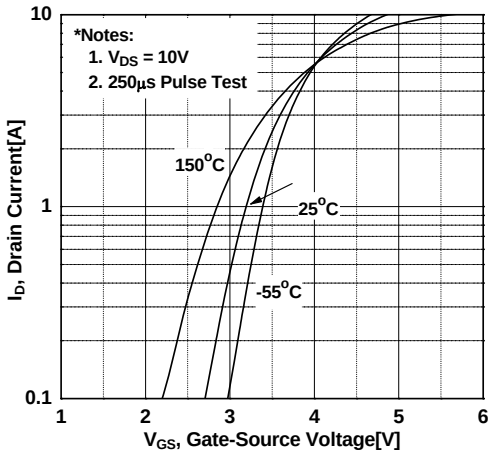


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

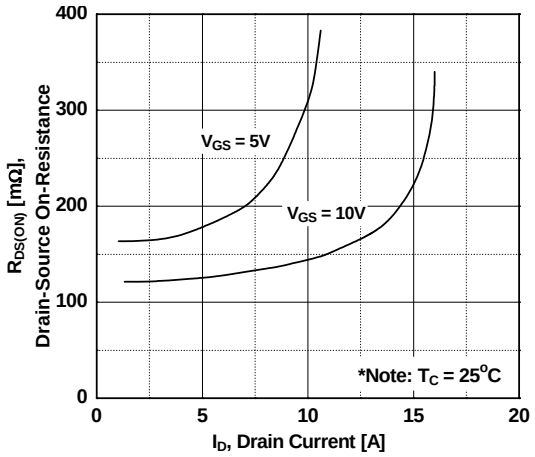


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

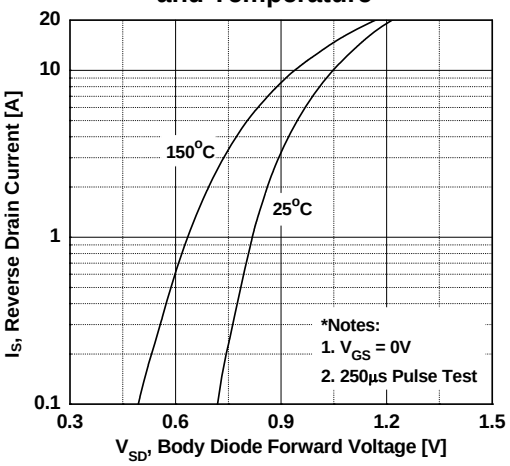


Figure 5. Capacitance Characteristics

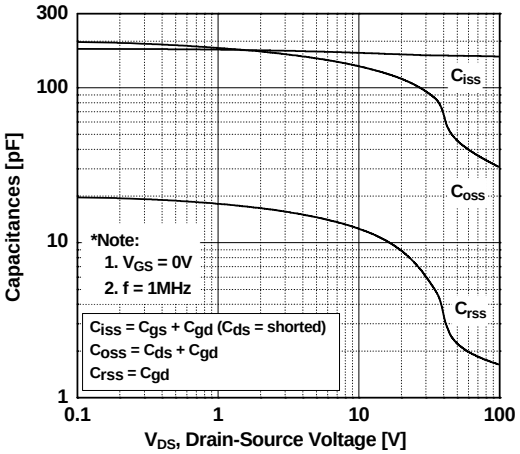
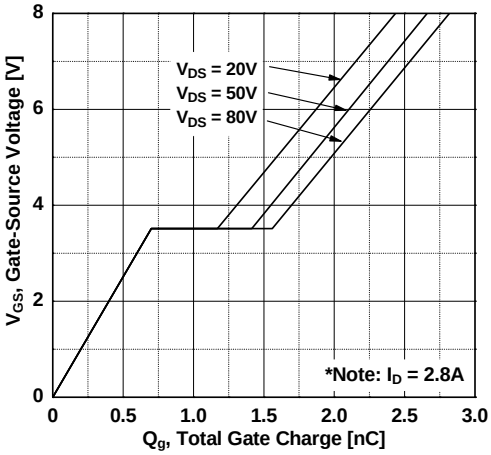


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

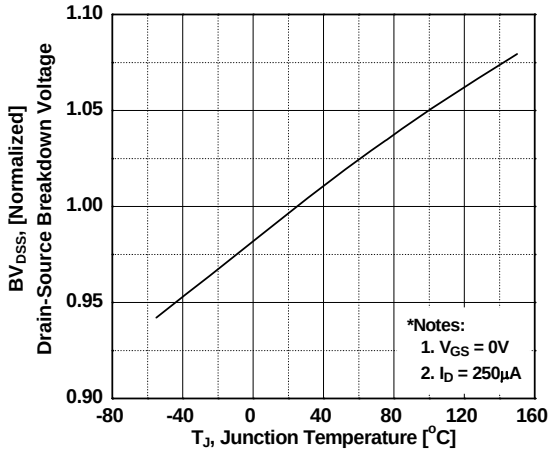


Figure 8. On-Resistance Variation vs. Temperature

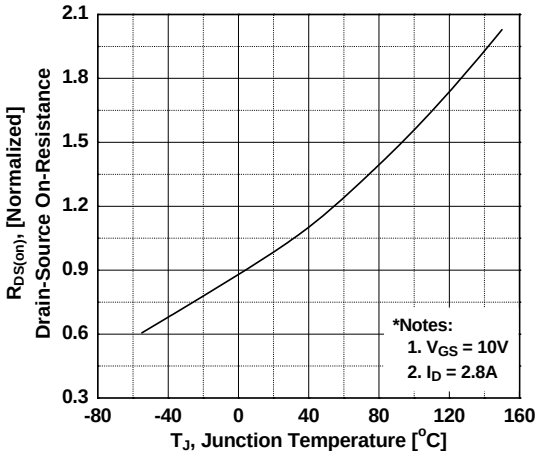


Figure 9. Maximum Safe Operating Area vs. Case Temperature

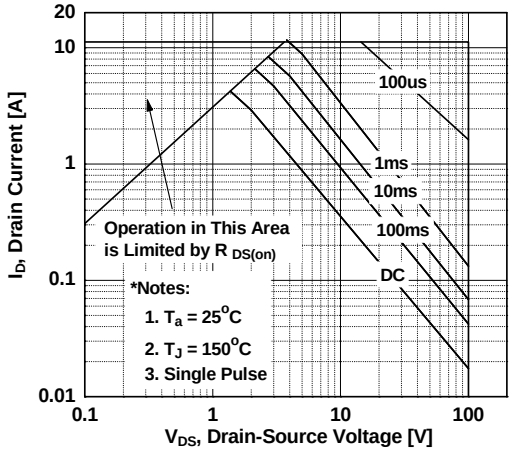


Figure 10. Maximum Drain Current

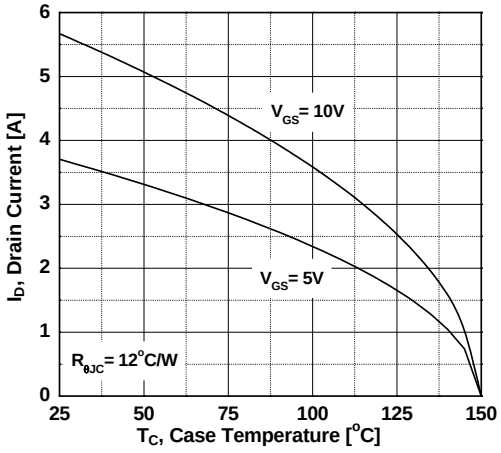


Figure 11. Eoss vs. Drain to Source Voltage

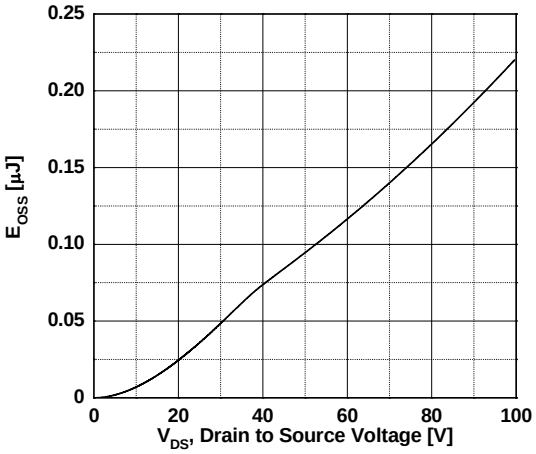
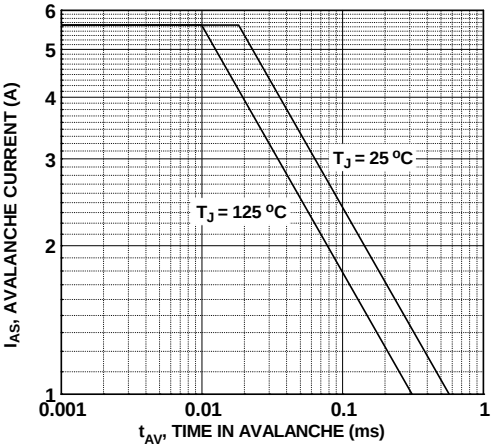
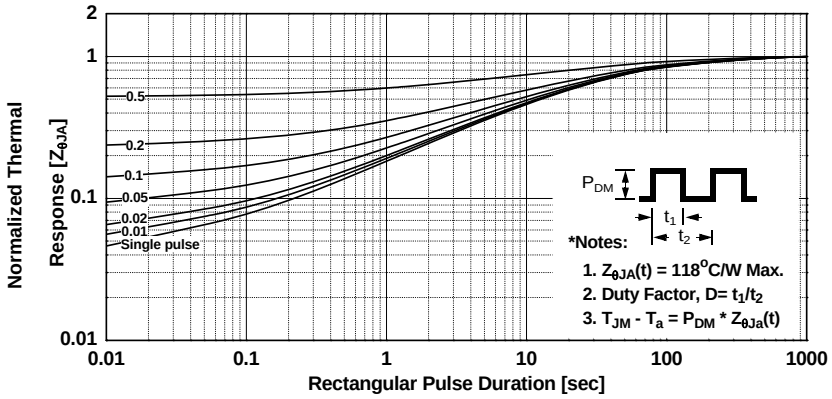


Figure 12. Unclamped Inductive Switching Capability

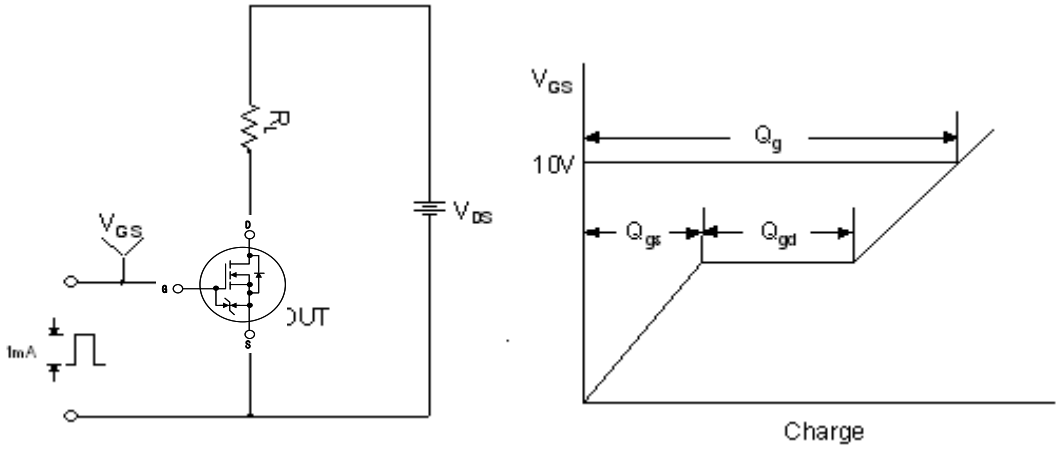


Typical Performance Characteristics (Continued)

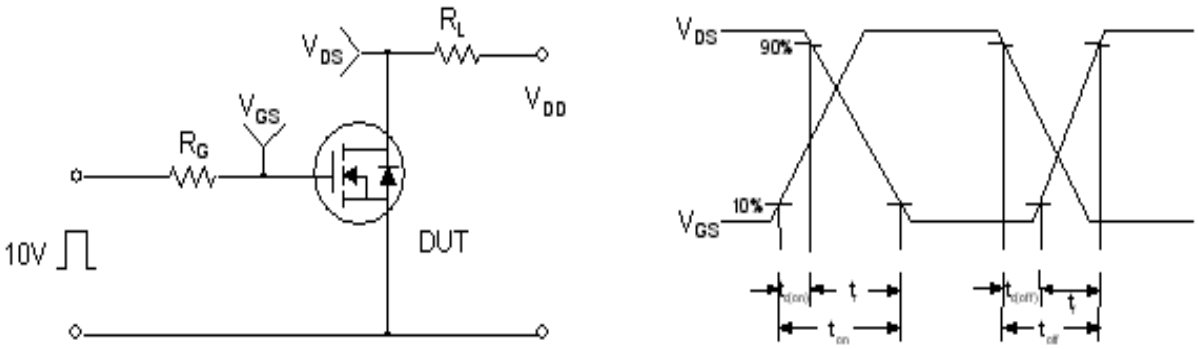
Figure 13. Transient Thermal Response Curve



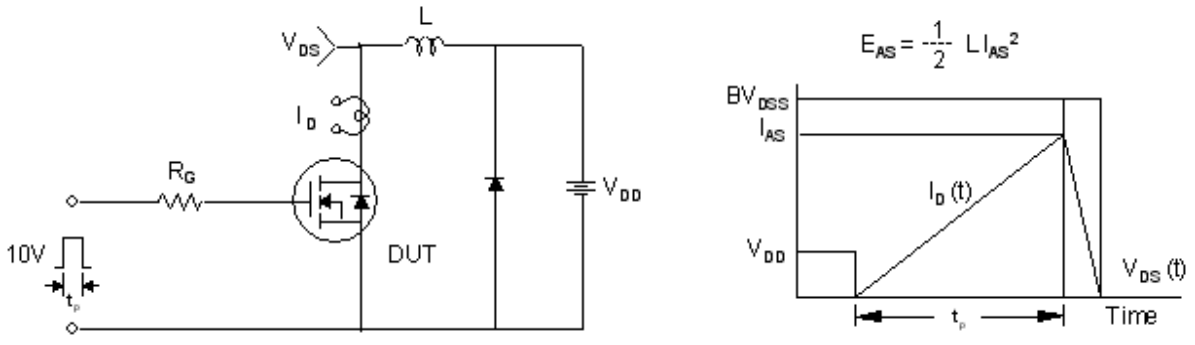
Gate Charge Test Circuit & Waveform



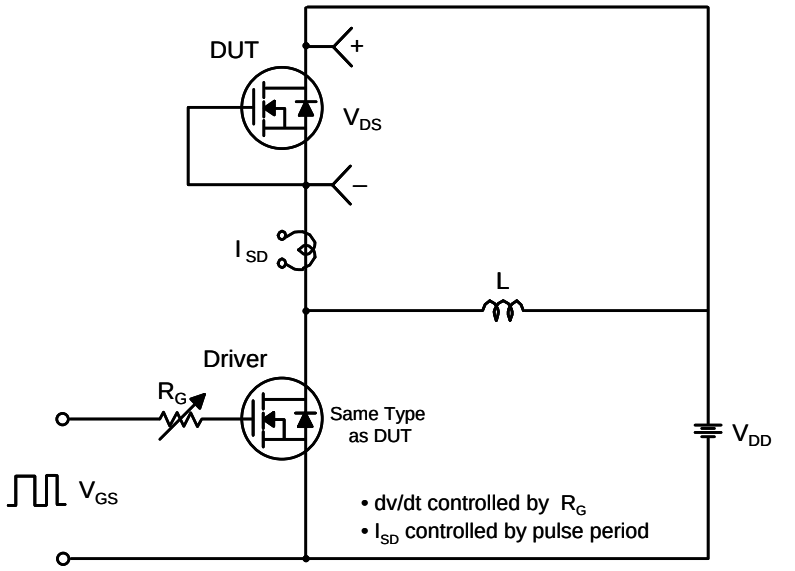
Resistive Switching Test Circuit & Waveforms

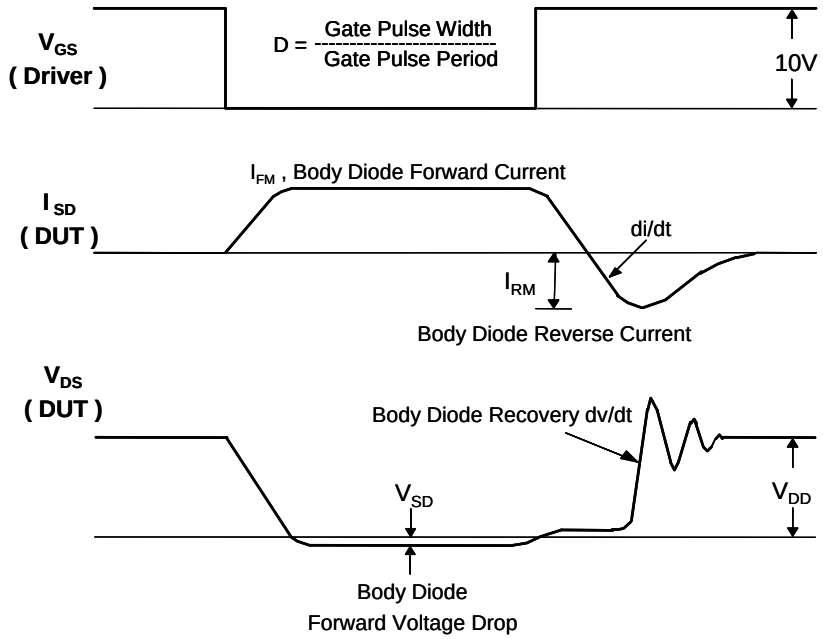


Unclamped Inductive Switching Test Circuit & Waveforms

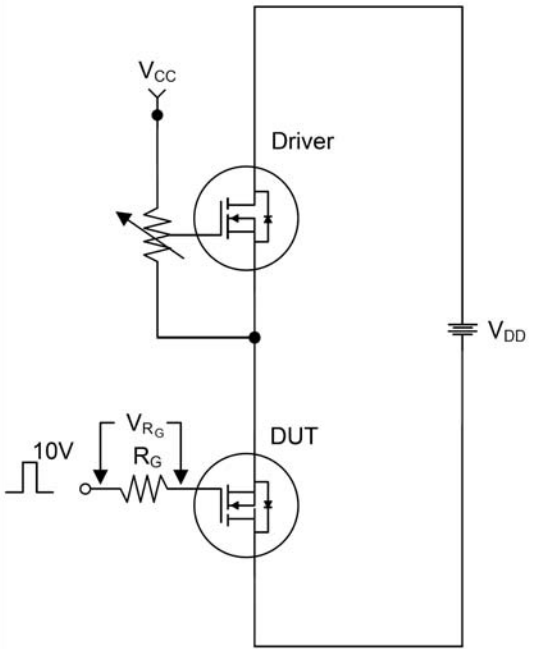


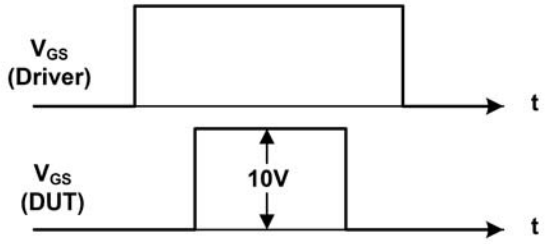
Peak Diode Recovery dv/dt Test Circuit & Waveforms





Total Gate Charge Qsync. Test Circuit & Waveforms

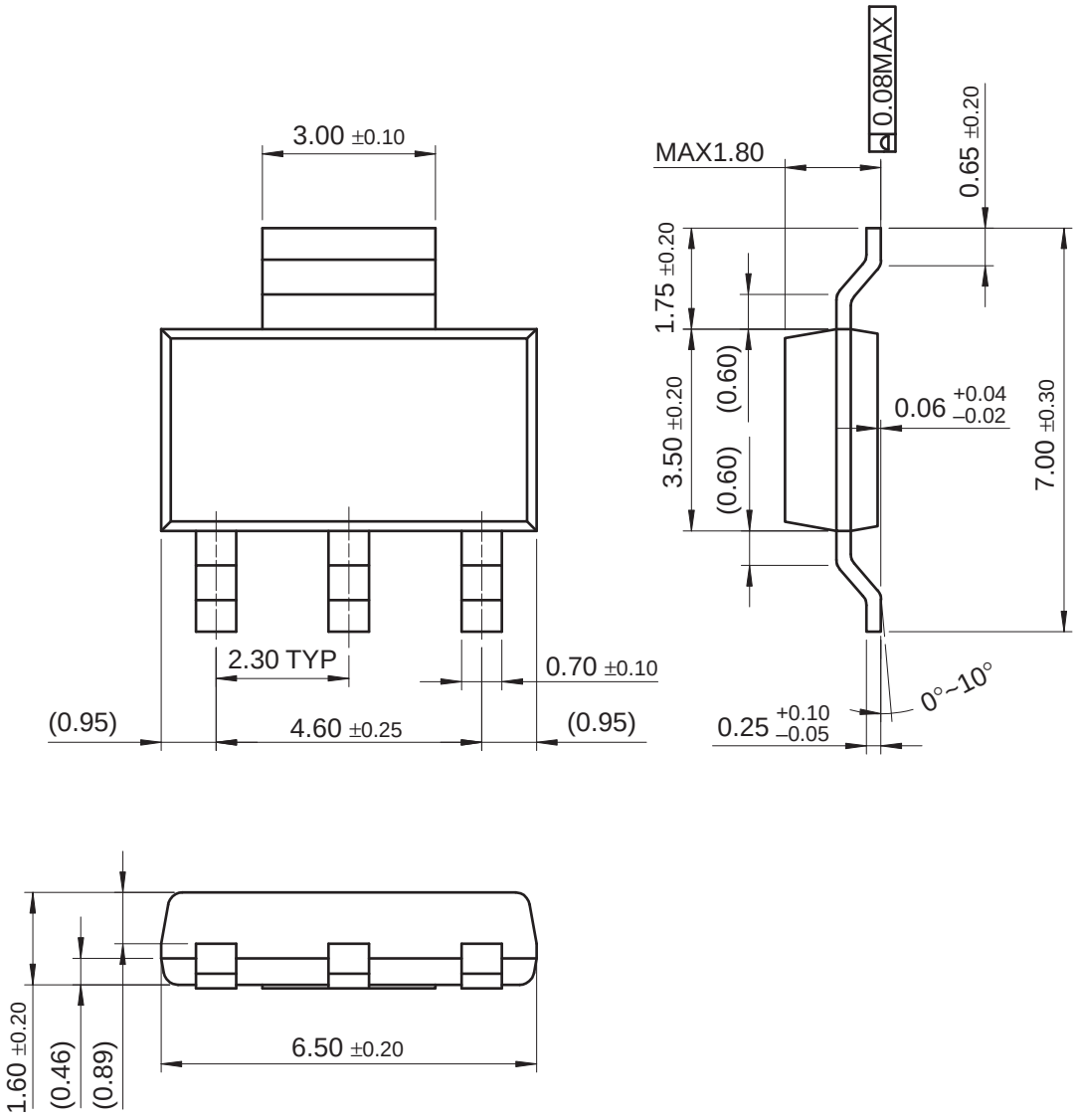




$$Qsync = \frac{1}{R_G} \cdot \int V_{R_G}(t)\ dt$$

Mechanical Dimensions

SOT-223



FAIRCHILD SEMICONDUCTOR®

TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

2Cool™
AccuPower™
AX-CAP®*
BitSiC™
Build it Now™
CorePLUS™
CorePOWER™
CROSSVOLT™
CTL™
Current Transfer Logic™
DEUXPEED®
Dual Cool™
EcoSPARK®
EfficentMax™
ESBC™
Fairchild®
Fairchild Semiconductor®
FACT Quiet Series™
FACT®
FAST®
FastvCore™
FETBench™
FPS™
F-PFS™
FRFET®
Global Power Resource^{SM}
Green Bridge™
Green FPS™
Green FPS™ e-Series™
G*max*™
GTO™
IntelliMAX™
ISOPLANAR™
Marking Small Speakers Sound Louder and Better™
MegaBuck™
MICROCOUPLER™
MicroFET™
MicroPak™
MicroPak2™
MillerDrive™
MotionMax™
mWSaver™
OptoHiT™
OPTOLOGIC®
OPTOPLANAR®
PowerTrench®
PowerXS™
Programmable Active Droop™
QFET®
QS™
Quiet Series™
RapidConfigure™
Saving our world, 1mW/W/kW at a time™
SignalWise™
SmartMax™
SMART START™
Solutions for Your Success™
SPM®
STEALTH™
SuperFET®
SuperSOT™-3
SuperSOT™-6
SuperSOT™-8
SupreMOS®
SyncFET™
Sync-Lock™
SYSTEM GENERAL ®*
TinyBoost™
TinyBuck™
TinyCalc™
TinyLogic®
TINYOPTO™
TinyPower™
TinyPWM™
TinyWire™
TranSiC®
TriFault Detect™
TRUECURRENT®*
µSerDes™
UHC®
Ultra FRFET™
UniFET™
VCX™
VisualMax™
VoltagePlus™
XS™

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS
Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I64